

DIO7299

Ultra-Small, Low-Input Voltage, Low r_{ON} Load Switch

Features

- Low-Input Voltage: 1.2V to 5.5V
- Ultra-Low ON-State Resistance
 - $r_{ON}=36m\Omega$ at $V_{IN}=5.0V$
 - $r_{ON}=38m\Omega$ at $V_{IN}=4.2V$
 - $r_{ON}=39m\Omega$ at $V_{IN}=3.6V$
 - $r_{ON}=46m\Omega$ at $V_{IN}=2.5V$
 - $r_{ON}=58m\Omega$ at $V_{IN}=1.8V$
 - $r_{ON}=150m\Omega$ at $V_{IN}=1.2V$
- DC Current Up to 2A
- Ultra-Low Quiescent Current: 67nA at 1.8V
- Ultra-Low Shutdown Current: 36nA at 1.8V
- Low Control Input Thresholds Enable Use of 1.2V/1.8V/3.6V/4.2V/5.0V Logic
- Controlled Slew Rate to Avoid Inrush Current
- Package: WLCSP-4 (0.9mm x 0.9mm, 0.5mm Pitch, 0.5mm Height)

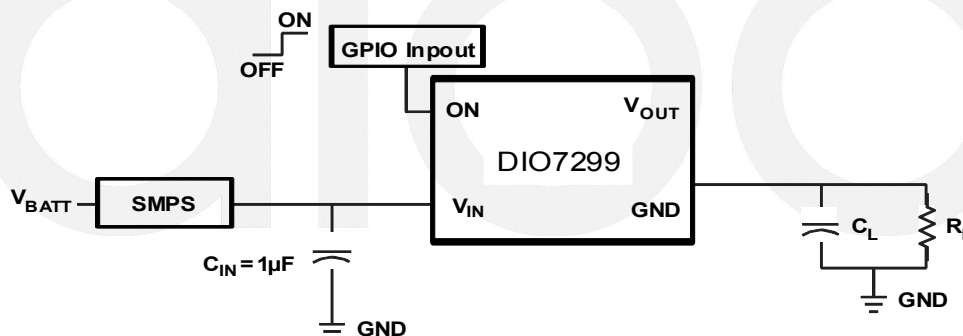
Descriptions

DIO7299 device is low R_{ON} MOSEFT controlled by external logic pin, allowing optimization of battery life, and portable device autonomy. It includes a P-channel MOSFET that operates over an input voltage range of 1.2V to 5.5V. An on/off input (ON) controls the switch that can interface with low voltage control signals. A 120 Ω on chip load resistor is added for output quick discharge when the switch is turned off. DIO7299 is packaged in WLCSP-4 with 0.5mm pitch. It is characterized for operation over the free-air temperature range of -40°C to 85°C.

Applications

- Cellular Phones
- GPS Devices
- Digital Cameras
- Peripheral Ports
- Portable Instrumentation
- RF Modules
- Personal Digital Assistants (PDAs)
- MP3 Players

Applications





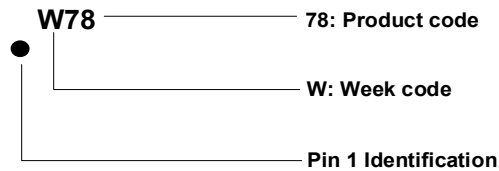
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Ordering Information

Order Part Number	Top Marking		T _A	Package	
DIO7299WL4	W78	Green	-40 to 85°C	WLCSP-4	Tape & Reel, 3000

Marking Definition



Pin Assignment

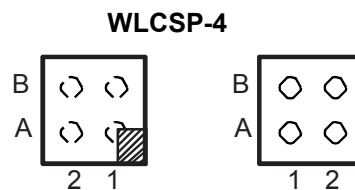


Figure 1. Top View & Bottom View

Pin Descriptions

Name	NO.	Description
V _{OUT}	A1	Switch output
V _{IN}	A2	Switch input, bypass this input with a ceramic capacitor to ground
GND	B1	Ground
ON	B2	Switch control input, active high



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Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Rating" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Symbol	Parameter	Rating	Unit
V_{IN}	Input voltage	-0.3 to 6	V
V_{OUT}	Output voltage	$V_{IN}+0.3$	V
V_{ON}	Input voltage	-0.3 to 6	V
P_D	Power dissipation at $T_A=25^{\circ}\text{C}$	0.48	W
I_{MAX}	Maximum continuous switch current	2	A
T_A	Operating free air temperature range	-40 to 85	$^{\circ}\text{C}$
T_{lead}	Maximum lead temperature (10s soldering time)	300	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-45 to 145	$^{\circ}\text{C}$
θ_{JA}	Thermal Resistance	189.1	$^{\circ}\text{C/W}$
ESD	HBM: All Pins	± 4000	V
	CDM	± 2000	
	MM	± 200	
Latch up		± 400	mA

Recommend Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended Operating conditions are specified to ensure optimal performance to the datasheet specifications. DIOO does not Recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Rating	Unit
V_{IN}	Input voltage range	1.2 to 5.5	V
V_{OUT}	Output voltage range	V_{IN}	V
V_{IH}	High level input voltage, ON	0.95 to 5.5	V
V_{IL}	Low level input voltage, ON	0.4	V
C_{IN}	Input capacitor	1	μF



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Electrical Characteristics

$V_{IN}=1.2V$ to $5.5V$, $T_A = -40^{\circ}C$ to $85^{\circ}C$, unless otherwise specified.

Symbol	Parameter	Conditions	T_A	Min.	Typ.	Max.	Unit
I_{IN}	Quiescent current	$I_{OUT}=0$, $V_{IN}=V_{ON}$	$25^{\circ}C$		31		nA
				Full		43	
			$25^{\circ}C$		67		
				Full		85	
			$25^{\circ}C$		176		
				Full		212	
			$25^{\circ}C$		210		
				Full		255	
			$25^{\circ}C$		260		
				Full		314	
$I_{IN(OFF)}$	OFF-state supply current	$V_{ON}=GND$, $OUT=Open$	$25^{\circ}C$		18		nA
				Full		216	
			$25^{\circ}C$		36		
				Full		306	
			$25^{\circ}C$		92		
				Full		700	
			$25^{\circ}C$		110		
				Full		800	
			$25^{\circ}C$		145		
				Full		1000	
$I_{IN(LEAKAGE)}$	OFF-state switch current	$V_{ON}=GND$, $V_{OUT}=0$	$25^{\circ}C$		18		nA
				Full		211	
			$25^{\circ}C$		35		
				Full		306	
			$25^{\circ}C$		92		
				Full		700	
			$25^{\circ}C$		110		
				Full		800	
			$25^{\circ}C$		145		
				Full		1000	
R_{ON}	ON-state resistance	$I_{OUT}=-200mA$	$25^{\circ}C$		36		m Ω
				Full		48	
			$25^{\circ}C$		38		
				Full		51	
			$25^{\circ}C$		39		
				Full		55	
			$25^{\circ}C$		46		
				Full		65	
			$25^{\circ}C$				
				Full			



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			$V_{IN}=1.8V$	25°C		58		
				Full			78	
			$V_{IN}=1.2V$	25°C		150		
				Full			220	
R_{PD}	Output pull down resistance	$V_{IN}=3.3V, V_{ON}=0, I_{OUT}=30mA$	25°C			95	120	Ω
I_{ON}	ON input leakage current	$V_{ON}=1.2V$ to 5.5V or GND	Full				48	nA

Specifications subject to change without notice.

Switching Characteristics

$R_{L_CHIP}=120\Omega$, $T_A = 25^\circ C$, unless otherwise specified.

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
V _{IN} =1.2V							
t _{ON}	Turn on time	R _L =500Ω	C _L =0.1μF		655		μs
			C _L =1μF		710		
			C _L =3.3μF		782		
t _{OFF}	Turnoff time	R _L =500Ω	C _L =0.1μF		17		μs
			C _L =1μF		93		
			C _L =3.3μF		281		
t _r	V _{OUT} rise time	R _L =500Ω	C _L =0.1μF		489		μs
			C _L =1μF		473		
			C _L =3.3μF		519		
t _f	V _{OUT} fall time	R _L =500Ω	C _L =0.1μF		28		μs
			C _L =1μF		261		
			C _L =3.3μF		992		
V _{IN} =1.8V							
t _{ON}	Turn on time	R _L =500Ω	C _L =0.1μF		420		μs
			C _L =1μF		454		
			C _L =3.3μF		495		
t _{OFF}	Turnoff time	R _L =500Ω	C _L =0.1μF		11		μs
			C _L =1μF		67		
			C _L =3.3μF		175		
t _r	V _{OUT} rise time	R _L =500Ω	C _L =0.1μF		339		μs
			C _L =1μF		331		
			C _L =3.3μF		347		
t _f	V _{OUT} fall time	R _L =500Ω	C _L =0.1μF		23		μs



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			$C_L=1\mu F$		225		
			$C_L=3.3\mu F$		757		
V_{IN}=2.5V							
t _{ON}	Turn on time	R _L =500Ω	C _L =0.1μF		317		μs
			C _L =1μF		341		
			C _L =3.3μF		366		
t _{OFF}	Turnoff time	R _L =500Ω	C _L =0.1μF		10		μs
			C _L =1μF		61		
			C _L =3.3μF		141		
t _r	V _{OUT} rise time	R _L =500Ω	C _L =0.1μF		279		μs
			C _L =1μF		269		
			C _L =3.3μF		274		
t _f	V _{OUT} fall time	R _L =500Ω	C _L =0.1μF		23		μs
			C _L =1μF		228		
			C _L =3.3μF		649		
V_{IN}=3.0V							
t _{ON}	Turn on time	R _L =500Ω	C _L =0.1μF		275		μs
			C _L =1μF		293		
			C _L =3.3μF		314		
t _{OFF}	Turnoff time	R _L =500Ω	C _L =0.1μF		9		μs
			C _L =1μF		61		
			C _L =3.3μF		120		
t _r	V _{OUT} rise time	R _L =500Ω	C _L =0.1μF		258		μs
			C _L =1μF		254		
			C _L =3.3μF		252		
t _f	V _{OUT} fall time	R _L =500Ω	C _L =0.1μF		22		μs
			C _L =1μF		224		
			C _L =3.3μF		636		
V_{IN}=3.6V							
t _{ON}	Turn on time	R _L =500Ω	C _L =0.1μF		245		μs
			C _L =1μF		257		
			C _L =3.3μF		276		
t _{OFF}	Turn off time	R _L =500Ω	C _L =0.1μF		9		μs
			C _L =1μF		58		
			C _L =3.3μF		104		
t _r	V _{OUT} rise time	R _L =500Ω	C _L =0.1μF		241		μs



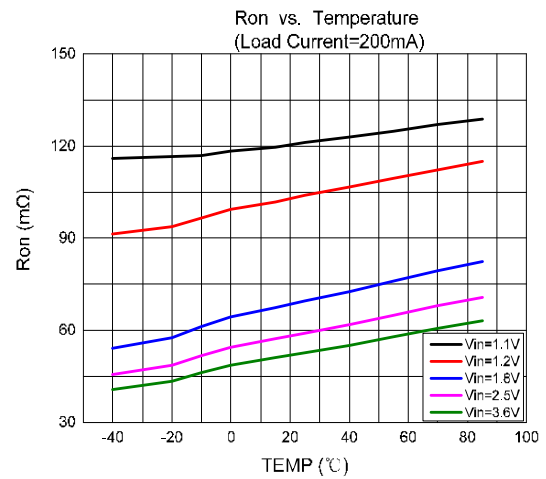
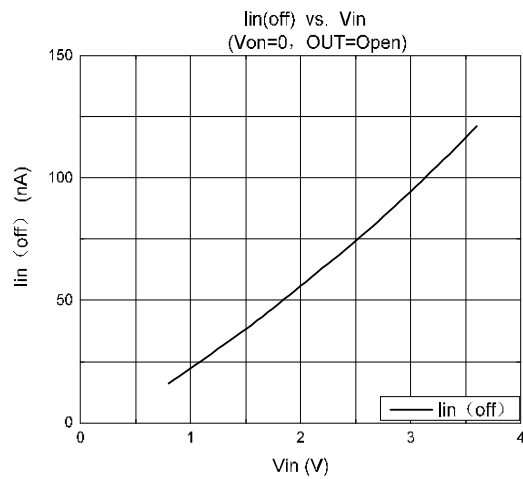
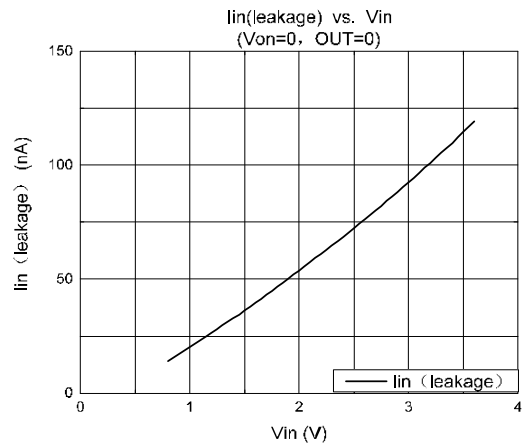
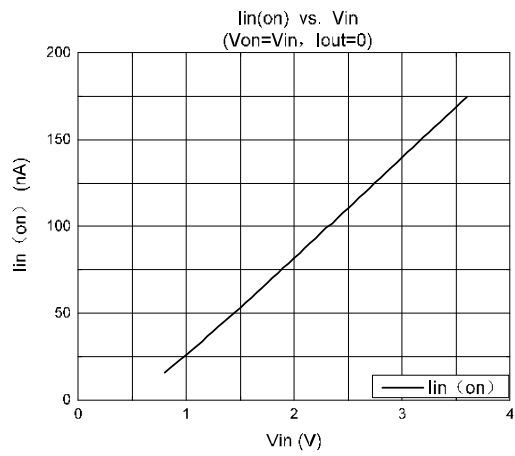
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			C _L =1μF		238		
			C _L =3.3μF		233		
t _f	V _{OUT} fall time	R _L =500Ω	C _L =0.1μF		22		μs
			C _L =1μF		221		
			C _L =3.3μF		593		
V _{IN} =4.2V							
t _{ON}	Turn on time	R _L =500Ω	C _L =0.1μF		230		μs
			C _L =1μF		242		
			C _L =3.3μF		250		
t _{OFF}	Turn off time	R _L =500Ω	C _L =0.1μF		9		μs
			C _L =1μF		59		
			C _L =3.3μF		89		
t _r	V _{OUT} rise time	R _L =500Ω	C _L =0.1μF		230		μs
			C _L =1μF		222		
			C _L =3.3μF		218		
t _f	V _{OUT} fall time	R _L =500Ω	C _L =0.1μF		22		μs
			C _L =1μF		221		
			C _L =3.3μF		525		
V _{IN} =5.0V							
t _{ON}	Turn on time	R _L =500Ω	C _L =0.1μF		203		μs
			C _L =1μF		213		
			C _L =3.3μF		220		
t _{OFF}	Turn off time	R _L =500Ω	C _L =0.1μF		8		μs
			C _L =1μF		50		
			C _L =3.3μF		73		
t _r	V _{OUT} rise time	R _L =500Ω	C _L =0.1μF		220		μs
			C _L =1μF		216		
			C _L =3.3μF		207		
t _f	V _{OUT} fall time	R _L =500Ω	C _L =0.1μF		21		μs
			C _L =1μF		213		
			C _L =3.3μF		489		

Specifications subject to change without notice.

Typical Performance Characteristics



Detailed Description

Overview

DIO7299 is a low ON-state resistance (r_{ON}) load switch with controlled turn on. It contains a P-channel MOSFET and can be turned on with a range of battery from 1.2V to 5.5V. An on/off input (ON) controls the switch, which can interface with low-voltage control signals. A 120Ω on-chip load resistor is added for output quick discharge when the switch is turned off.

Functional Block Diagram

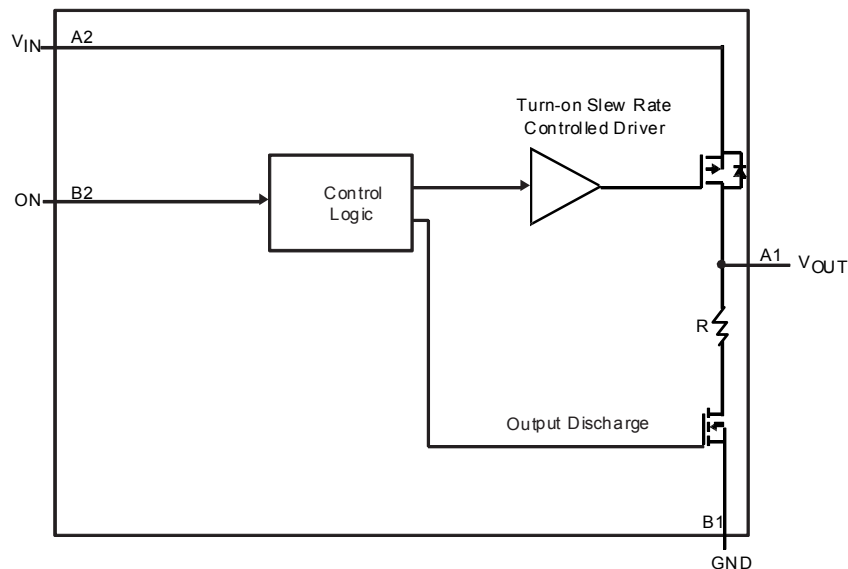


Figure 2. Block Diagram

Feature Description

ON/OFF Control

The state of the switch is controlled by the ON pin. When there is no fault, activating ON can let the switch to be in the on state. ON is active HI and has a low threshold making it capable of interfacing with low-voltage signals. The ON pin is compatible with standard GPIO logic threshold. It can be used with any microcontroller with 1.2V, 1.8V, 2.5V, 3.3V GPIOs.

Device Functional Modes

Table 1 lists the functional modes of the DIO7299.

Table 1. Function Table

ON (Control Input)	V_{IN} to V_{OUT}	V_{OUT} to GND
L	OFF	ON
H	ON	OFF

Application and Implementation

Application Information

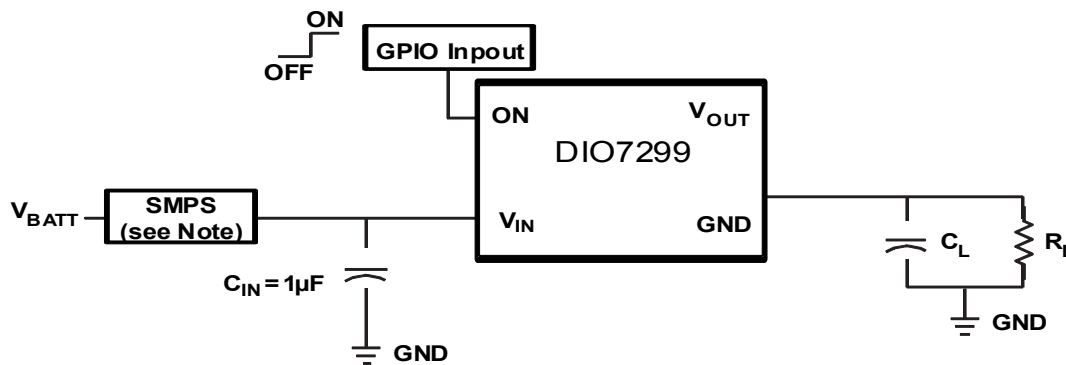
Input Capacitor

When the switch turns on into a discharged load capacitor or short-circuit, a capacitor needs to be placed between V_{IN} and GND to limit the voltage drop on the input supply caused by transient in-rush currents. A $1\mu F$ ceramic capacitor, C_{IN} , placed close to the pins is usually sufficient. C_{IN} 's higher values can be used to further reduce the voltage drop during high current application. It is recommended to have an input capacitor approximately 10 times higher than the output capacitor to avoid excessive voltage drop when switching heavy loads.

Output Capacitor

A C_{IN} greater than C_L is highly recommended when the integral body diode in the PMOS switch. When the system supply is removed, a C_L greater than C_{IN} can cause V_{OUT} to exceed V_{IN} . This could result in current flow through the body diode from V_{OUT} to V_{IN} .

Typical Application



Note: Switched mode power supply

Figure 3. Powering a Downstream Module

Design Requirements

Table 2 lists the design parameters for the DIO7299 device.

Table 2. Design Parameters

Design Parameter	Example Value
V_{IN}	1.8V
Load Current	0.3A
Ambient Temperature	25°C



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Detailed Design Procedure

V_{IN} to V_{OUT} Voltage Drop

The voltage drop from V_{IN} to V_{OUT} is determined by the ON-resistance of the device and the load current. The r_{ON} can be found in Electrical Characteristics and is dependent on temperature. When the value of r_{ON} is found, Equation 1 can be used to calculate the voltage drop across the device:

$$\Delta V = I_{LOAD} \times r_{ON} \quad (1)$$

Where

- ΔV = Voltage drop across the device
- I_{LOAD} = Load current
- r_{ON} = ON-resistance of the device

At $V_{IN}=1.8V$, the DIO7299 has a r_{ON} value of $58m\Omega$. Using this value and the defined load current, the above equation can be evaluated:

$$\Delta V = 0.30 A \times 58 m\Omega \quad (2)$$

Where,

$$\Delta V = 17.4mV$$

Therefore, the voltage drop across the device will be 17.4mV.

Power Supply Recommendations

The DIO7299 is designed to operate with a V_{IN} range of 1.2V to 5.5V. This supply must be well regulated and placed as close to the device terminals as possible. It must also be able to withstand all transient and load currents, using a recommended input capacitance of $1\mu F$ if necessary. If the supply is more than a few inches from the device terminals, additional bulk capacitance may be required in addition to the ceramic bypass capacitors. If additional bulk capacitance is required, an electrolytic, tantalum, or ceramic capacitor of $10\mu F$ may be sufficient.

Layout

Layout Guidelines

All traces should be as short as possible for best performance. To be most effective, the input and output capacitors should be placed close to the DIO7299 to minimize the effects that parasitic trace inductances may have on normal and short circuit operation. Using wide traces for V_{IN} , V_{OUT} , and GND helps minimize the parasitic electrical effects along with minimizing the case to ambient thermal impedance.

Layout Example

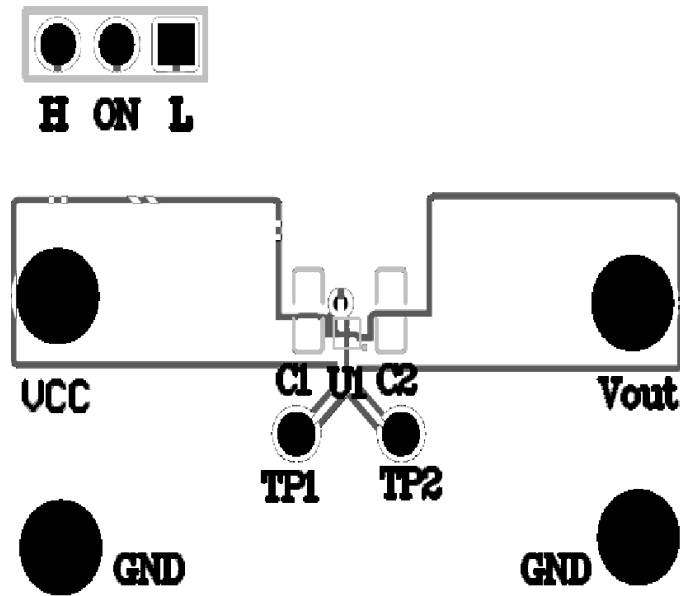
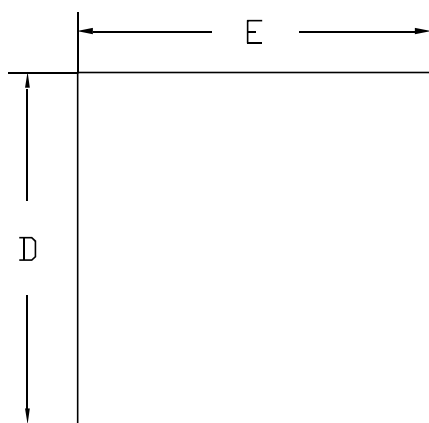
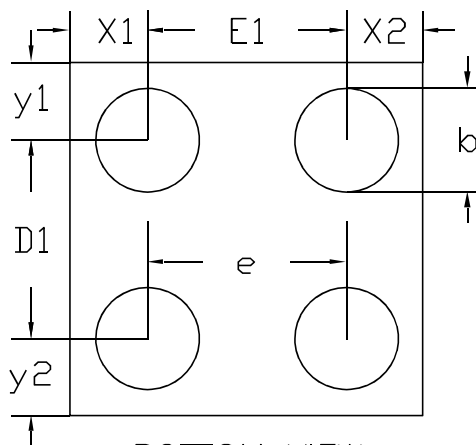


Figure 4. Recommended Board Layout

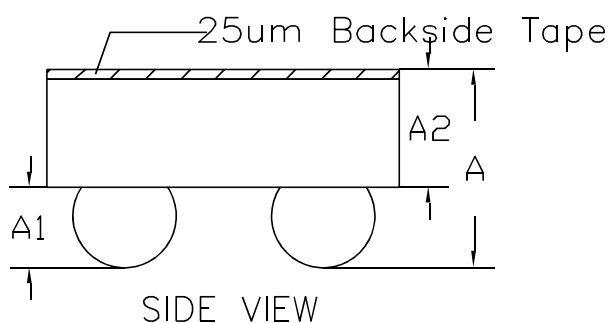
Physical Dimensions: WLCSP-4



TOP VIEW
(MARK SIDE)



BOTTOM VIEW
(BALL SIDE)



SIDE VIEW

COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)			
Symbol	MIN	NOM	MAX
A	0.460	0.500	0.540
A1	0.182	0.202	0.222
A2	0.278	0.298	0.318
D	0.868	0.888	0.908
D1	0.500 BSC		
E	0.868	0.888	0.908
E1	0.500 BSC		
b	0.230	0.260	0.290
e	0.500 BSC		
x1	0.194 REF		
x2	0.194 REF		
y1	0.194 REF		
y2	0.194 REF		



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CONTACT US

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